## **PSMN012-60MS**

# N-channel 60 V 12 mΩ standard level MOSFET in LFPAK33 19 December 2019 Product data sheet

### 1. General description

Standard level enhancement mode N-channel MOSFET in LFPAK33 package. This product is designed and qualified for use in a wide range of motor, industrial, communications and domestic equipment.

#### 2. Features and benefits

- · High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources
- LFPAK33 package is footprint compatible with other 3.3 mm footprint types
- Qualified to 175 °C

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C	-	-	60	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	-	-	53	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>	-	-	75	W
Tj	junction temperature		-55	-	175	°C
Static charac	teristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 15 A; $T_j$ = 25 °C; Fig. 11	-	10	12	mΩ
Dynamic cha	racteristics					•
Q <sub>GD</sub>	gate-drain charge	I <sub>D</sub> = 15 A; V <sub>DS</sub> = 48 V; V <sub>GS</sub> = 10 V;	-	8.5	-	nC
Q <sub>G(tot)</sub>	total gate charge	T <sub>j</sub> = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	24.8	-	nC

## 5. Pinning information

**Table 2. Pinning information** 

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	Source		D
2	S	Source		
3	S	Source		G—(F)
4	G	Gate		mbb076 S
mb	D	Mounting base; connected to drain	1 2 3 4 LFPAK33 (SOT1210)	



#### N-channel 60 V 12 m $\Omega$ standard level MOSFET in LFPAK33

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package						
	Name	Description	Version				
PSMN012-60MS		Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMN012-60MS	M12S60

## 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	60	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	60	V
$V_{GS}$	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	75	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	53	Α
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	37	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	211	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode			'		
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	53	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	211	Α
Avalanche r	uggedness			'		
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$I_D$ = 53 A; $V_{sup} \le 60$ V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[1]	-	34.3	mJ

<sup>[1]</sup> Single-pulse avalanche rating limited by maximum junction temperature of 175  $^{\circ}\text{C}.$ 

#### N-channel 60 V 12 mΩ standard level MOSFET in LFPAK33

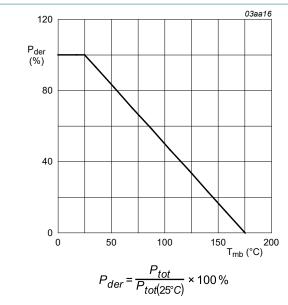
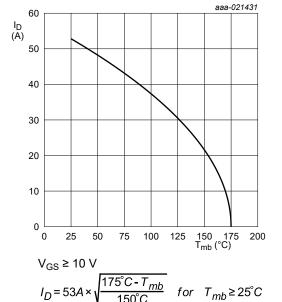
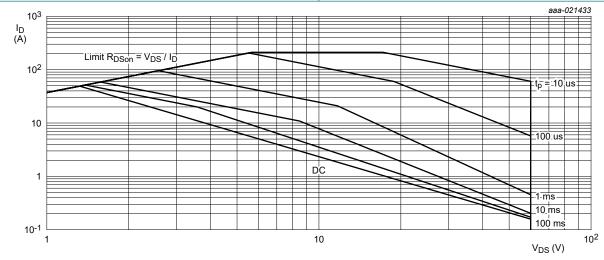


Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $I_D = 53A \times \sqrt{\frac{175^{\circ}C - T_{mb}}{150^{\circ}C}}$  for  $T_{mb} \ge 25^{\circ}C$ 

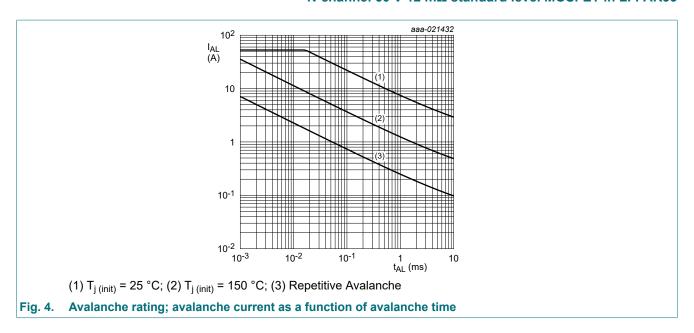
Fig. 2. Continuous drain current as a function of mounting base temperature



 $T_{mb}$  = 25 °C;  $I_{DM}$  is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

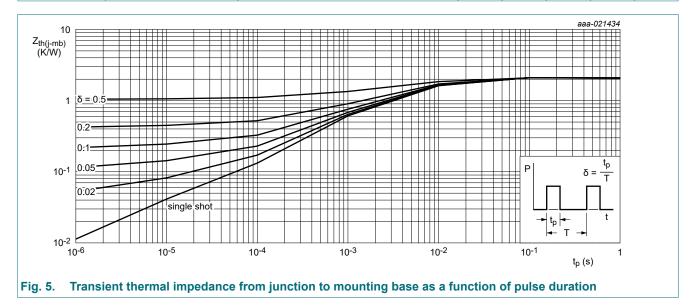
#### N-channel 60 V 12 mΩ standard level MOSFET in LFPAK33



#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	1.82	2	K/W



#### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static charact	eristics		•	•			
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		60	-	-	V
,	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$		54	-	-	V

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Symbol	Parameter	Conditions	M	lin	Тур	Max	Unit
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; Fig. 9;$ Fig. 10	2.	.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-		-	4.5	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1		-	-	V
I <sub>DSS</sub>	drain leakage current	$\begin{array}{llllllllllllllllllllllllllllllllllll$	μA				
		V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-		-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	$V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ - 2 100 $V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ - 2 100 $I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ - 10 12 $I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ 27	nA			
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-		2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	1	-		10	12	mΩ
			-		-	27	mΩ
Dynamic ch	naracteristics						
Q <sub>G(tot)</sub>	total gate charge		-		24.8	-	nC
Q <sub>GS</sub>	gate-source charge		-		5.6	-	nC
Q <sub>GD</sub>	gate-drain charge		-		8.5	-	nC
C <sub>iss</sub>	input capacitance	Fig. 11 $V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ °C};$ Fig. 12 $I_D = 15 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 13}; \text{ Fig. 14}$ $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; \text{ Fig. 15}$ $V_{DS} = 45 \text{ V}; R_L = 3 \Omega; V_{GS} = 10 \text{ V};$	-		1222	1625	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-		167	200	pF
C <sub>rss</sub>	reverse transfer capacitance		-		104	143	pF
t <sub>d(on)</sub>	turn-on delay time		-		6.6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$	-		9.7	-	ns
t <sub>d(off)</sub>	turn-off delay time		-		17.4	-	ns
t <sub>f</sub>	fall time		-		10.5	-	ns
Source-drai	in diode						1
V <sub>SD</sub>	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$	-		0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 15 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-		19.5	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 25 V; T <sub>j</sub> = 25 °C	-		16.6	-	nC
		1				- 1	

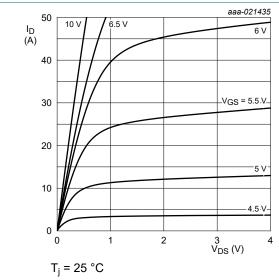


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

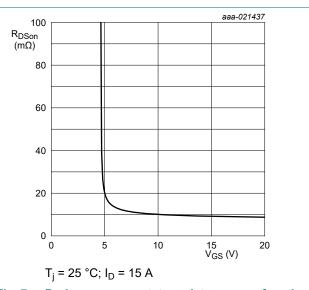


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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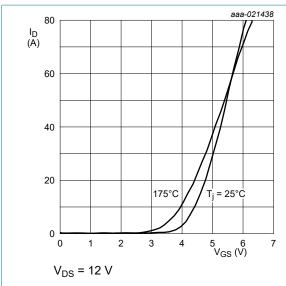


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

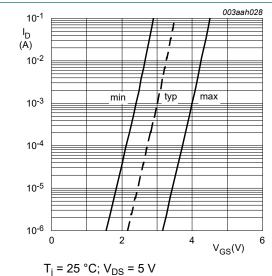
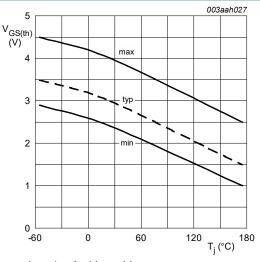


Fig. 10. Sub-threshold drain current as a function of gate-source voltage



 $I_D = 1 \text{ mA}$ ;  $V_{DS} = V_{GS}$ 

Fig. 9. Gate-source threshold voltage as a function of junction temperature

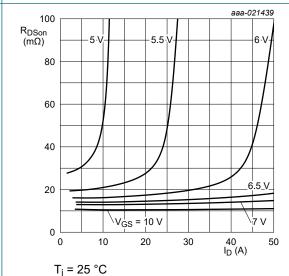


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

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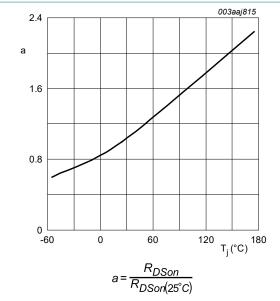


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

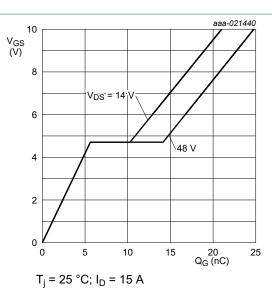


Fig. 13. Gate-source voltage as a function of gate charge; typical values

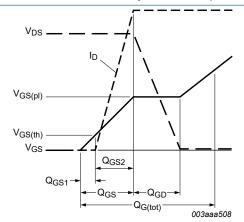


Fig. 14. Gate charge waveform definitions

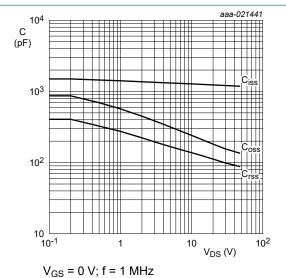


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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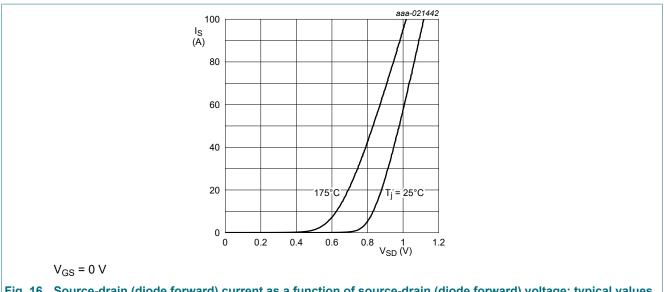


Fig. 16. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

#### N-channel 60 V 12 mΩ standard level MOSFET in LFPAK33

## 11. Package outline

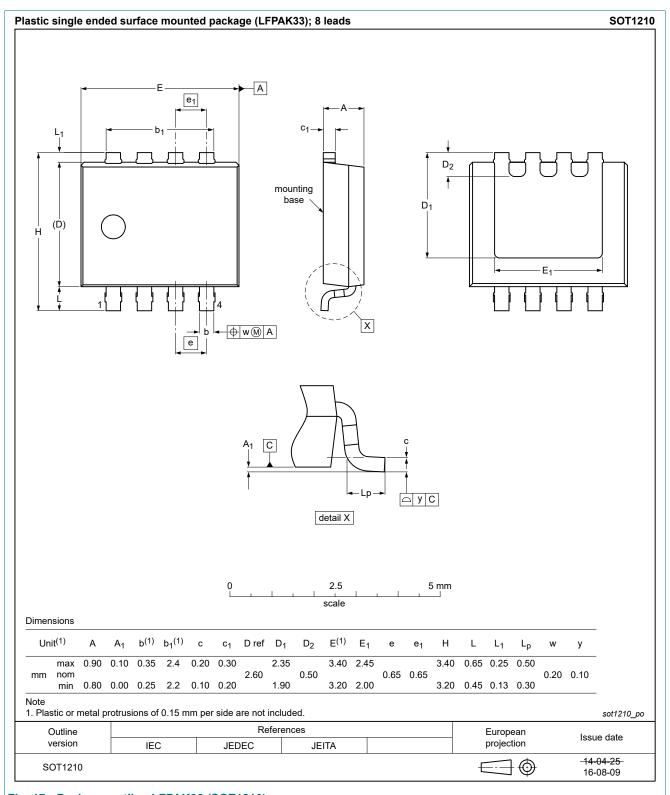
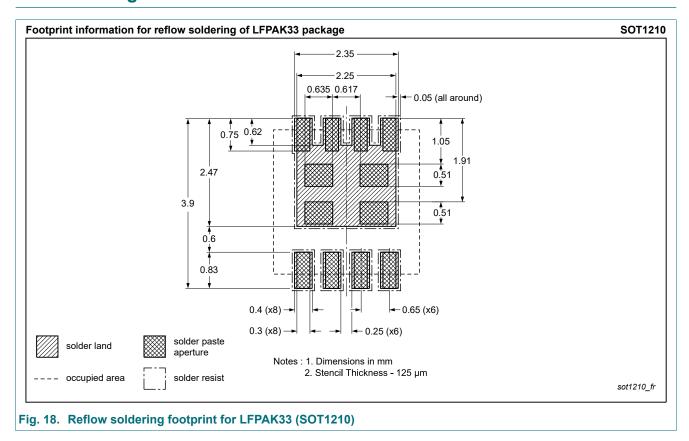


Fig. 17. Package outline LFPAK33 (SOT1210)

#### N-channel 60 V 12 m $\Omega$ standard level MOSFET in LFPAK33

## 12. Soldering



#### N-channel 60 V 12 mΩ standard level MOSFET in LFPAK33

#### 13. Legal information

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